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# Numerical investigations of the multi-layer graphene as a thermal interface material and an elector-magnetic field shield layer for 3D power supply on chip applications

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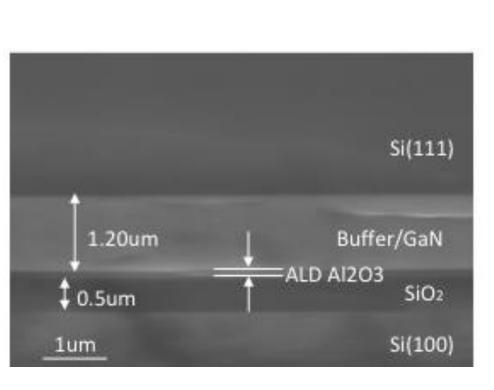
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#### INTRODUCTION

# > Advantages of 3D Power SoC

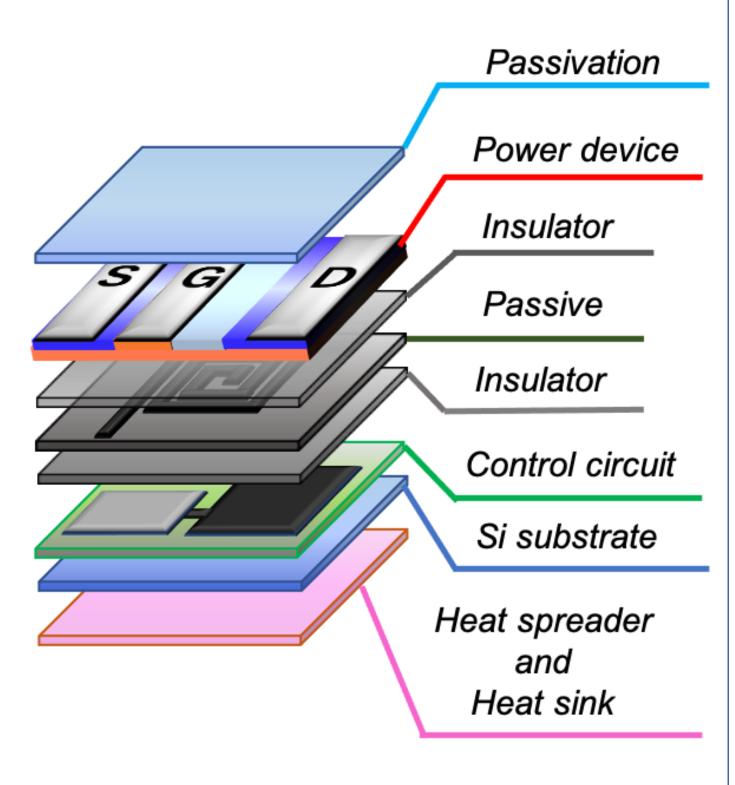
- High efficiency at high frequency switching
- High power density (miniaturization)



Direct bonding of GaN - Si(100) [1]

# > Challenges

- Heterogenous integration
- Heat removal
- Electromagnetic noise shielding

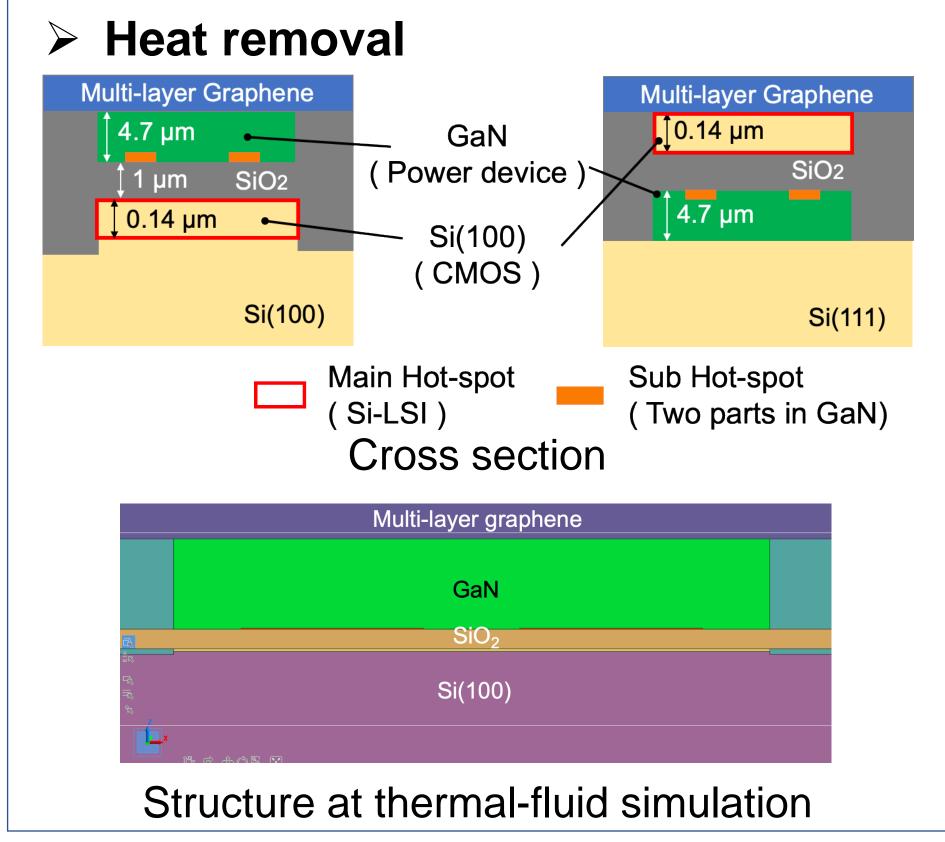


3D power SoC [2]

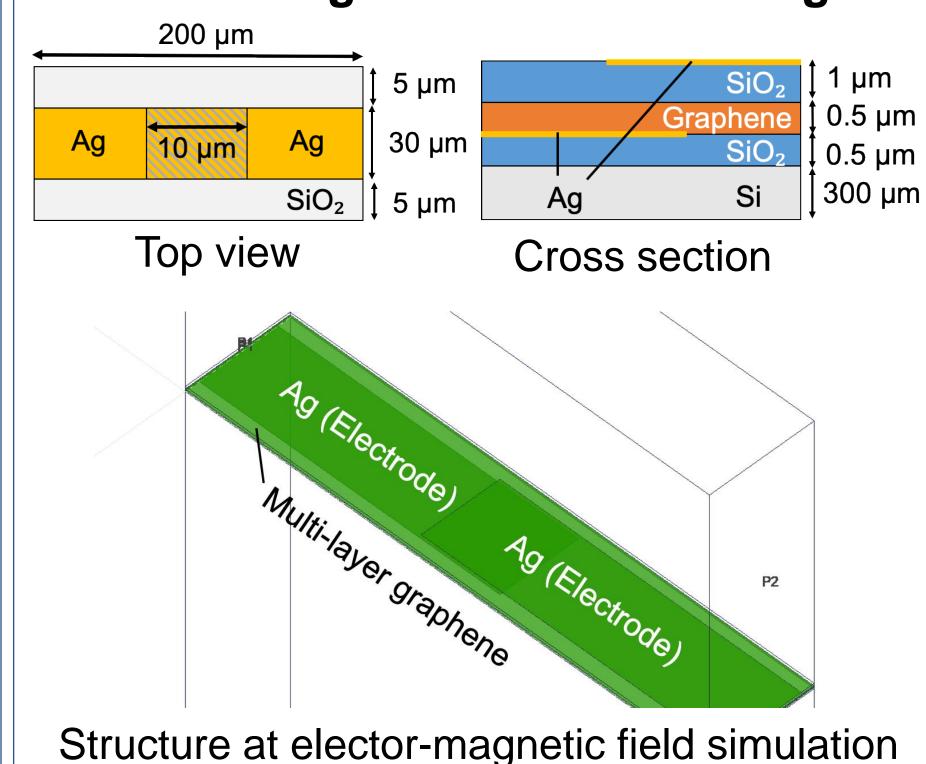
# Multi-layer graphene

[1] R. Ishito, K. Ono, and S. Matsumoto, IEEE CPMT Symposium Japan 2019, ECR Session 12, 2019. [2] K. Hiura, Y. Ikeda, Y. Hino, and S. Matsumoto, Japanese J Applied Physics, vo.56, 04CR13, 2017.

# DESIGN DETAILS

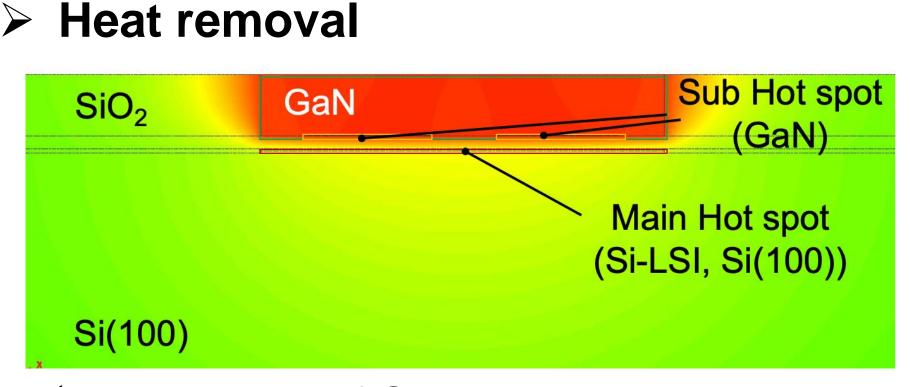


# > Electromagnetic noise shielding

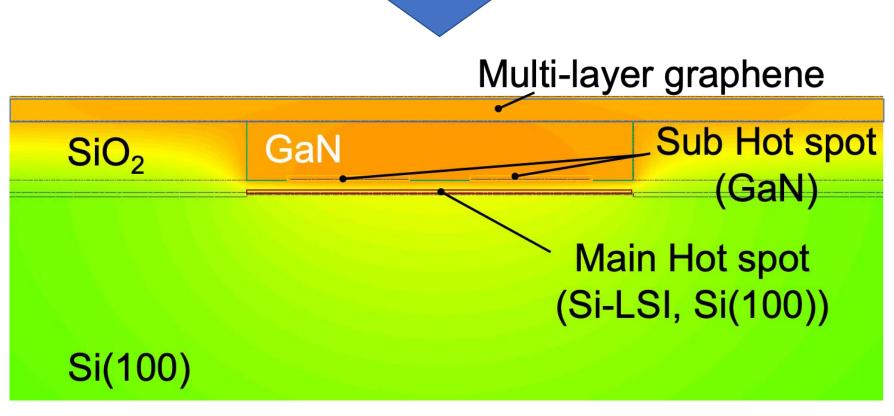


## SIMULATION RESULTS

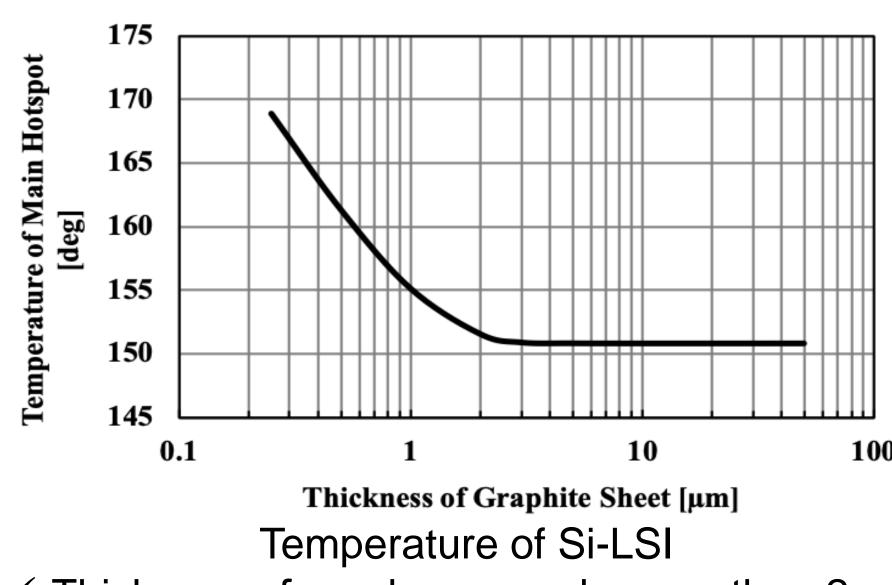
-50



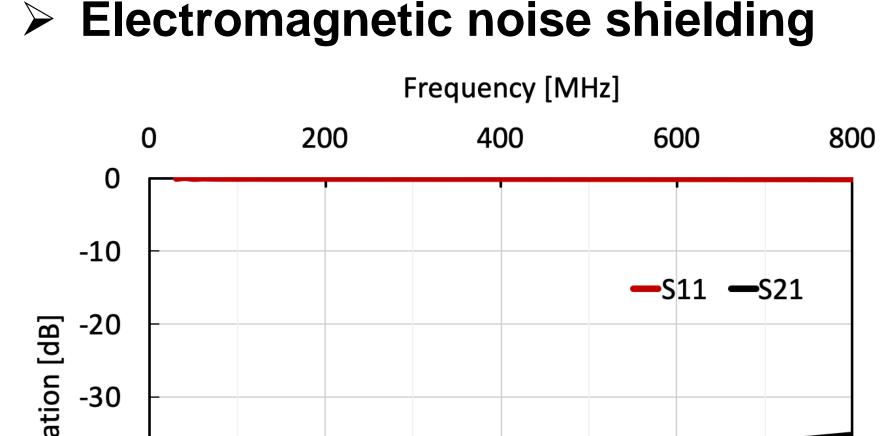
✓ Temperature of GaN is 192 deg without multi-layer graphene.



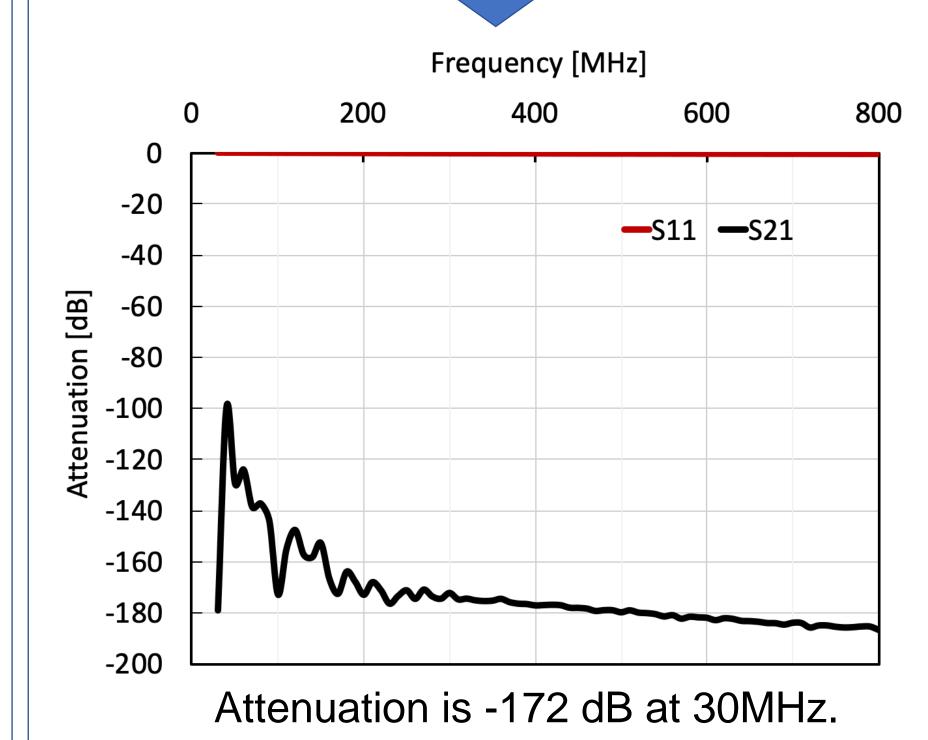
✓ Temperature of GaN is 174 deg with multi-layer graphene.



✓ Thickness of graphene needs more than 2µm.



Attenuation is -64 dB at 30MHz.



✓ Noise attenuation with multi-layer graphene is 108 dB higher than without it.

# SUMMARY

- ✓ We can remove the heat of hot-spot in GaN power device by putting GaN on Si-LSI and using multi-layer graphene.
- ✓ Multi-layer graphene enables to shield electromagnetic noise.

## ACKNOWLEDGEMENTS / CONTACT

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